



2.0A SINGLE CHANNEL CURRENT-LIMITED POWER SWITCH

Description

The AP2301 and AP2311 are single channel current-limited integrated high-side power switches optimized for Universal Serial Bus (USB) and other hot-swap applications. The family of devices complies with USB standards and is available with both polarities of Enable input.

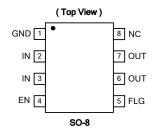
The devices have fast short-circuit response time for improved overall system robustness, and have integrated output discharge function to ensure completely controlled discharging of the output voltage capacitor. They provide a complete protection solution for applications subject to heavy capacitive loads and the prospect of short circuit, and offer reverse current blocking, over-current, over-temperature and short-circuit protection, as well as controlled rise time and undervoltage lockout functionality. A 7ms deglitch capability on the opendrain Flag output prevents false over-current reporting and does not require any external components.

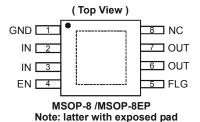
All devices are available in SO-8, MSOP-8, MSOP-8EP, U-DFN3030-8 and U-DFN2020-6 packages.

Features

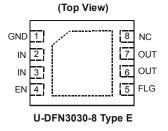
- Single channel current-limited power switch
- Output discharge function
- Fast short-circuit response time: 2µs
- 2.5A accurate current limiting
- Reverse current blocking
- 70mΩ on-resistance
- Input voltage range: 2.7V 5.5V
- Built-in soft-start with 0.6ms typical rise time
- Over-current and thermal protection
- Fault report (FLG) with blanking time (7ms typ)
- ESD protection: 2kV HBM, 200V MM
- Ambient temperature range: -40°C to +85°C
- SO-8, MSOP-8, MSOP-8EP, U-DFN3030-8 and U-DFN2020-6: Available in "Green" Molding Compound (No Br, Sb)
 - Totally Lead-free & Fully RoHS Compliant (Notes 1 & 2)
 - Halogen and Antimony Free. "Green" Device (Note 3)
- UL Recognized, File Number E322375
- IEC60950-1 CB Scheme Certified

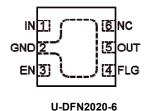
Pin Assignments





(dotted line)





Applications

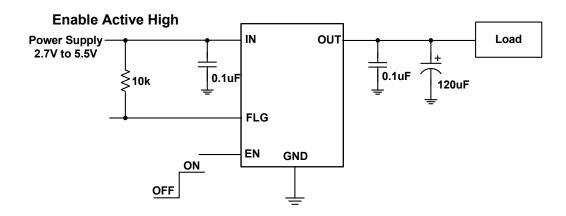
- LCD TVs & Monitors
- Set-Top-Boxes, Residential Gateways
- Laptops, Desktops, Servers, e-Readers, Printers, Docking Stations, HUBs

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Typical Applications Circuit



Available Options

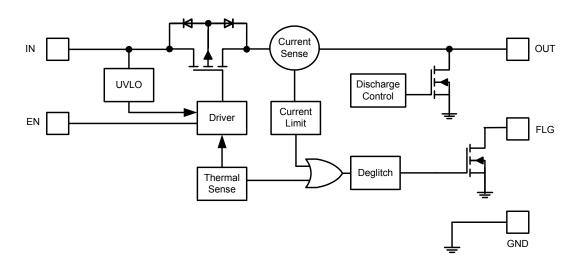
Part Number	Channel	Enable Pin (EN)	Recommended Maximum Continuous Load Current (A)	Typical Current Limit (A)	Package
AP2301	1	Active Low	2A	254	SO-8 MSOP-8 MSOP-8EP
AP2311	1	Active High	ZA	2.5A	WSOP-8EP U-DFN3030-8 U-DFN2020-6

Pin Descriptions

Pin	Pin Number		r	
Name	SO-8, MSOP-8	MSOP-8EP, U-DFN3030-8	U-DFN2020-6	Function
GND	1	1	2	Ground
IN	2, 3	2, 3	1	Voltage Input Pin; Connect a 0.1µF or larger ceramic capacitor from IN to GND as close as possible. (all IN pins must be tied together externally)
EN	4	4	3	Enable input, active low (AP2301) or active high (AP2311)
FLG	5	5	4	Over-temperature and over-current fault reporting with 7ms deglitch; active low opendrain output. FLG is disabled for 7ms after turn-on.
OUT	6, 7	6, 7	5	Voltage Output Pin All OUT pins must be tied together externally.
NC	8	8	6	NC: No Internal Connection; recommend tie to OUT pins
Exposed Pad	_	Exposed Pad	Exposed Pad	Exposed pad. It should be externally connected to GND and thermal mass for enhanced thermal impedance. It should not be used as electrical ground conduction path.



Functional Block Diagram



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Ratings	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD MM	Machine Model ESD Protection	200	V
V _{IN}	Input Voltage (Note 4)	-0.3 to 6.5	V
V _{OUT}	Output Voltage (Note 4)	-0.3 to (V _{IN} +0.3) or 6.5	V
V_{EN} , V_{FLG}	Enable Voltage (Note 4)	-0.3 to (V _{IN} +0.3) or 6.5	V
I _{LOAD}	Maximum Continuous Load Current	Internal Limited	A
$T_{J(MAX)}$	Maximum Junction Temperature	150	°C
T _{ST}	Storage Temperature Range (Note 5)	-65 to +150	°C

Notes:

- 4. All voltages referred to GND pin. Maximums are the lower of (V_{IN} +0.3) and 6.5V
- 5. UL Recognized Rating from -30°C to +70°C (Diodes qualified T_{ST} from -65°C to +150°C)

Caution: Stresses greater than the 'Absolute Maximum Ratings' specified above, may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.

Semiconductor devices are ESD sensitive and may be damaged by exposure to ESD events. Suitable ESD precautions should be taken when handling and transporting these devices.

Recommended Operating Conditions (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V_{IN}	Input voltage	2.7	5.5	V
I _{OUT}	Output Current	0	2	Α
VIL	EN Input Logic Low Voltage	0	0.8	V
V_{IH}	EN Input Logic High Voltage	2	V _{IN}	V
TA	Operating Ambient Temperature	-40	+85	°C



Electrical Characteristics (@T_A = +25 $^{\circ}$ C, V_{IN} = +5V, C_{IN} = 0.1 μ F, C_L = 1 μ F, unless otherwise specified.)

Symbol	Parameter	Test Condi	itions	Min	Тур	Max	Unit
V _{UVLO}	Input UVLO	V _{IN} rising		1.6	2.0	2.4	V
ΔV _{UVLO}	Input UVLO Hysteresis	V _{IN} decreasing			50		mV
I _{SHDN}	Input Shutdown Current	Disabled, OUT = open			0.1	1	μA
ΙQ	Input Quiescent Current	Enabled, OUT = open			60	100	μΑ
I _{LEAK}	Input Leakage Current	Disabled, OUT grounded			0.1	1	μΑ
I _{REV}	Reverse Leakage Current	Disabled, V _{IN} = 0V, V _{OUT} = 5V,	I _{REV} at V _{IN}		0.01	1	μA
		., -,,	T _A = +25°C		70	84	
		V_{IN} = 5V, I_{OUT} = 2.0A	-40°C ≤ T _A ≤ +85°C			105	
R _{DS(ON)}	Switch on-resistance		T _A = +25°C		90	108	mΩ
		$V_{IN} = 3.3V$, $I_{OUT} = 2.0A$	-40°C ≤ T _A ≤ +85°C			135	
I _{LIMIT}	Over-Load Current Limit (Note 6)	V _{IN} = 5V, V _{OUT} = 4.5V	-40°C ≤ T _A ≤ +85°C	2.05	2.50	2.85	Α
I _{Trig}	Current limiting trigger threshold	Output Current Slew rate (<100			2.5		Α
Ishort	Short-Circuit Current Limit	Enabled into short circuit	•		2.75		Α
T _{SHORT}	Short-circuit Response Time	V _{OUT} = 0V to I _{OUT} = I _{LIMIT} (OUT	shorted to ground)		2		μs
VIL	EN Input Logic Low Voltage	V _{IN} = 2.7V to 5.5V				0.8	V
V _{IH}	EN Input Logic High Voltage	V _{IN} = 2.7V to 5.5V		2			V
I _{LEAK-EN}	EN Input leakage	V _{IN} = 5V, V _{EN} = 0V and 5.5V			0.01	1	μA
I _{LEAK-O}	Output leakage current	Disabled, V _{OUT} = 0V			0.5	1	μA
T _{D(ON)}	Output turn-on delay time	$C_L = 1\mu F$, $R_{LOAD} = 5\Omega$			0.1		ms
T _R	Output turn-on rise time	$C_L = 1\mu F$, $R_{LOAD} = 5\Omega$			0.6	1.5	ms
T _{D(OFF)}	Output turn-off delay time	$C_L = 1\mu F$, $R_{LOAD} = 5\Omega$			0.1		ms
T _F	Output turn-off fall time	$C_L = 1\mu F, R_{LOAD} = 5\Omega$			0.05	0.1	ms
R _{FLG}	FLG output FET on-resistance	I _{FLG} = 10mA			20	40	Ω
I _{FOH}	FLG Off Current	V _{FLG} = 5V			0.01	1	μA
T _{Blank}	FLG blanking time	Assertion or deassertion due to temperature condition	o overcurrent and over-	4	7	15	ms
T _{DIS}	Discharge time	$C_L = 1\mu F$, $V_{IN} = 5V$, disabled to	V _{OUT} < 0.5V		0.6		ms
R _{DIS}	Discharge resistance (Note 7)	V _{IN} = 5V, disabled, I _{OUT} = 1mA			100		Ω
T _{SHDN}	Thermal Shutdown Threshold	Enabled			140		°C
T _{HYS}	Thermal Shutdown Hysteresis				20		°C
		SO-8 (Note 8)			96		°C/W
	The annual Desister of the state of the stat	MSOP-8 (Note 8)			130		°C/W
θ_{JA}	Thermal Resistance Junction-to- Ambient	MSOP-8-EP (Note 9)			92		°C/W
	7 11101011	U-DFN3030-8 (Note 9)			84		°C/W
		U-DFN2020-6 (Note 10)			90		°C/W

Notes:

^{6.} Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

^{7.} The discharge function is active when the device is disabled (when enable is de-asserted or during power-up power-down when V_{IN} < V_{UVLO}). The discharge function is active when the device is disabled (when enable is de-assited of adming power-up powe

plane.

10. Device mounted on 1"x1" FR-4 substrate PCB, 2oz copper, with minimum recommended padon top layer and thermal vias to bottom layer ground.



Typical Performance Characteristics

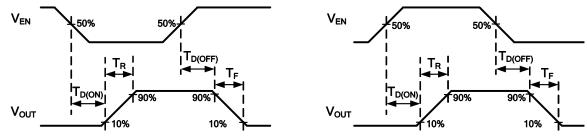
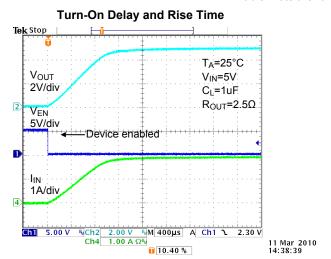
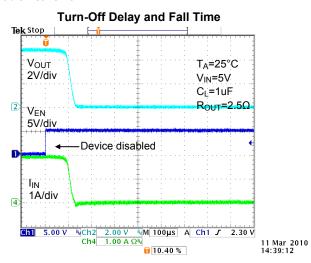


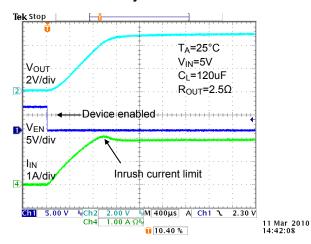
Figure 1. Voltage Waveforms: AP2301 (left), AP2311 (right)

All Enable Plots are for Enable Active Low

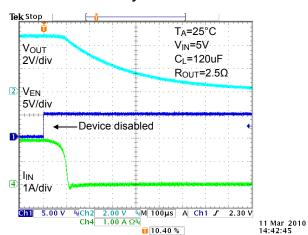




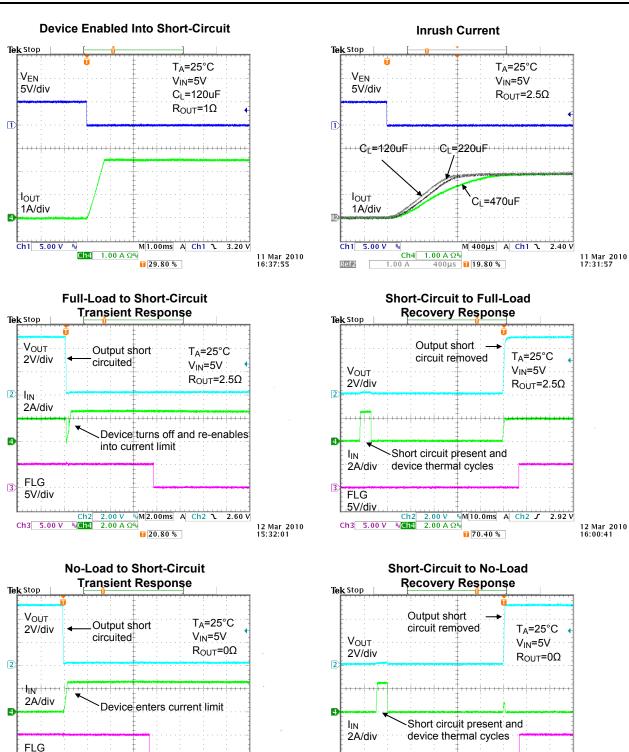
Turn-On Delay and Rise Time



Turn-Off Delay and Fall Time







3

5V/div

Ch2 2.00 V MM2.00ms A Ch2 \ 2.92 V Ch3 5.00 V MG14 2.00 A ΩM

19.60 %

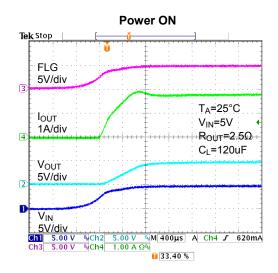
12 Mar 2010 16:31:34 FLG 5V/div

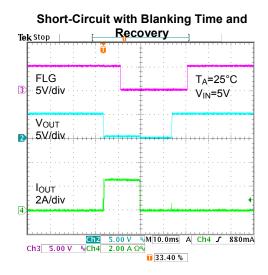
Ch2 2.00 V NCh3 5.00 V Ch4 2.00 A ΩN

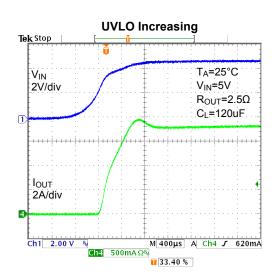
70.40 %

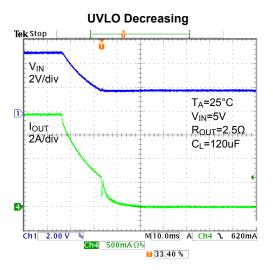
12 Mar 2010 16:47:07



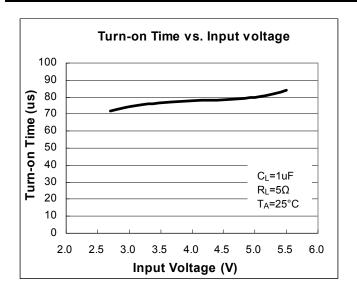


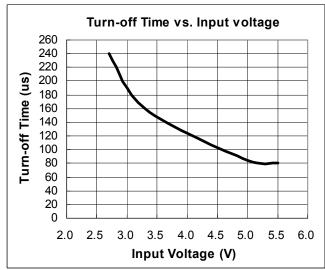


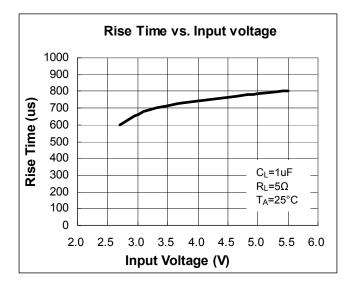


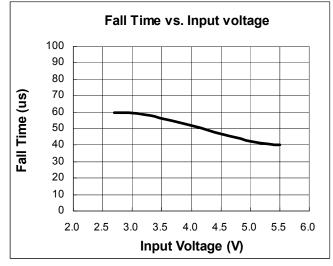




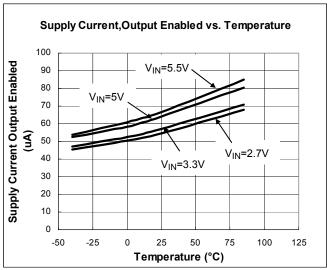


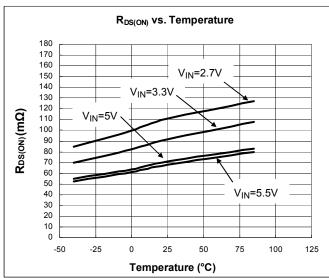


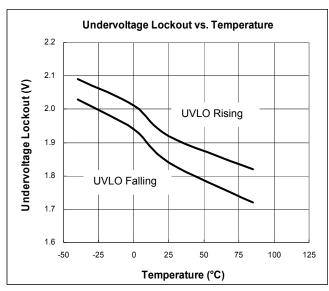


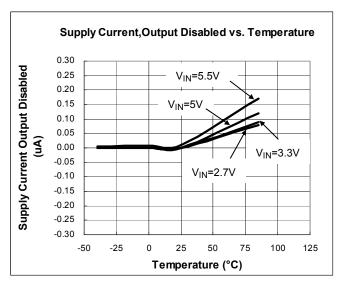


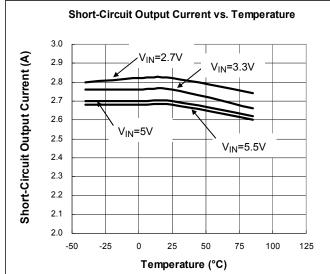


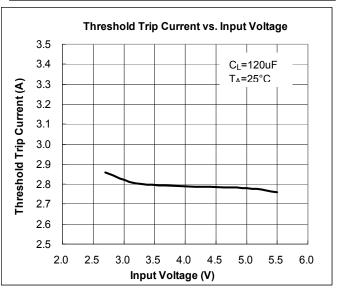














Application Information

Power Supply Considerations

A $0.1\mu F$ to $2.2\mu F$ X7R or X5R ceramic bypass capacitor placed between IN and GND, close to the device, is recommended. When an external power supply is used, or an additional ferrite bead is added to the input, high inrush current may cause voltage spikes higher than the device maximum input rating during short circuit condition. In this case a $2.2\mu F$ or bigger capacitor is recommended. Placing a high-value electrolytic capacitor on the input and output pin(s) is recommended when the output load is heavy. This precaution reduces power-supply transients that may cause ringing on the input. Additionally, bypassing the output with a $0.1\mu F$ to $1.0\mu F$ ceramic capacitor improves the immunity of the device to short circuit transients.

Over-Current and Short Circuit Protection

An internal sensing FET is employed to check for over-current conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an over-current condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault stays long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted to GND before the device is enabled or before V_{IN} has been applied. The AP2301/AP2311 senses the short circuit and immediately clamps output current to a certain safe level namely I_{LIMIT}.

In the second condition, an output short or an overload occurs while the device is enabled. At the instance the overload occurs, higher inrush current may flow for a very short period of time before the current limit function can react. The input capacitor(s) rapidly discharge through the device, activating current limit circuitry. Protection is achieved by momentarily opening the P-MOS high-side power switch and then gradually turning it on. After the current limit function has tripped (reached the over-current trip threshold), the device switches into current limiting mode and the current is clamped at I_{LIMIT}.

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold (I_{TRIG}) is reached or until the thermal limit of the device is exceeded. The AP2301/AP2311 is capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its current limiting mode and is set at I_{LIMIT}.

FLG Response

When an over-current or over-temperature shutdown condition is encountered, the FLG open-drain output goes active low after a nominal 7-ms deglitch timeout. The FLG output remains low until both over-current and over-temperature conditions are removed. Connecting a heavy capacitive load to the output of the device can cause a momentary over-current condition, which does not trigger the FLG due to the 7-ms deglitch timeout. The AP2301/AP2311 is designed to eliminate false over-current reporting without the need of external components to remove unwanted pulses.

Power Dissipation and Junction Temperature

The low on-resistance of the internal MOSFET allows the small surface-mount packages to pass large current. Using the maximum operating ambient temperature (T_A) and $R_{DS(ON)}$, the power dissipation can be calculated by:

 $P_D = R_{DS(ON)} \times I^2$

Finally, calculate the junction temperature:

 $T_J = PD \times R_{\theta JA} + T_A$

Where:

T_A= Ambient temperature °C

 $R_{\theta JA}$ = Thermal resistance

P_D = Total power dissipation

Thermal Protection

Thermal protection prevents the IC from damage when heavy-overload or short-circuit faults are present for extended periods of time. The AP2301/AP2311 implements a thermal sensing to monitor the operating junction temperature of the power distribution switch. Once the die temperature rises to approximately 140°C due to excessive power dissipation in an over-current or short-circuit condition the internal thermal sense circuitry turns the power switch off, thus preventing the power switch from damage. Hysteresis is built into the thermal sense circuit allowing the device to cool down approximately 20°C before the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed. The FLG open-drain output is asserted when an over-temperature shutdown or over-current occurs with 7-ms deglitch.

Under-Voltage Lockout (UVLO)

Under-voltage lockout function (UVLO) keeps the internal power switch from being turned on until the power supply has reached at least 2V, even if the switch is enabled. Whenever the input voltage falls below approximately 2V, the power switch is quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed.

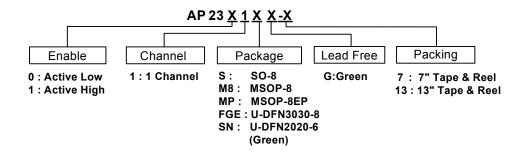


Application Information (cont.)

Discharge Function

The discharge function of the device is active when enable is disabled or de-asserted. The discharge function with the N-MOS power switch implementation is activated and offers a resistive discharge path for the external storage capacitor. This is designed for discharging any residue of the output voltage when either no external output resistance or load resistance is present at the output.

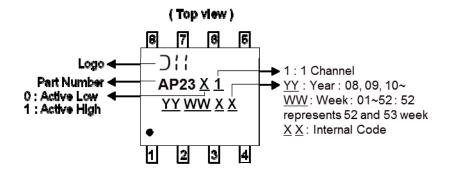
Ordering Information



Package		Docksoins	7"/13" Tape and Reel		
Part Number	Code	Packaging	Quantity	Part Number Suffix	
AP23X1SG-13	S	SO-8	2500/Tape & Reel	-13	
AP23X1M8G-13	M8	MSOP-8	2500/Tape & Reel	-13	
AP23X1MPG-13	MP	MSOP-8EP	2500/Tape & Reel	-13	
AP23X1FGEG-7	FGE	U-DFN3030-8 Type E	3000/Tape & Reel	-7	
AP23X1SN-7	SN	U-DFN2020-6	3000/Tape & Reel	-7	

Marking Information

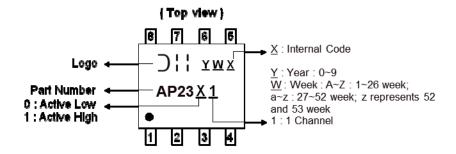
(1) SO-8



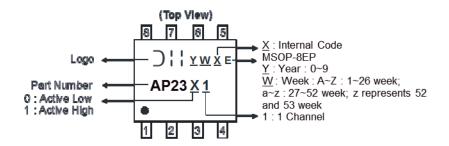


Marking Information (cont.)

(2) MSOP-8



(3) MSOP-8EP



(4) U-DFN3030-8 Type E

(Top View)

<u>XX</u> <u>YWX</u> XX: Identification Code

Y: Year : 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

a~z : 2/~52 week; z repre

<u>X</u> : A~Z : Green

Part Number	Package	Identification Code
AP2301FGEG-7	U-DFN3030-8	BB
AP2311FGEG-7	U-DFN3030-8	BC

(5) U-DFN2020-6

(Top View)

<u>XX</u> <u>YWX</u> XX: Identification Code

<u>Y</u> : Year : 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal Code

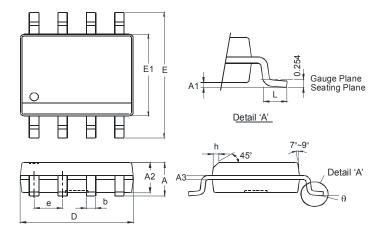
Part Number	Package	Identification Code
AP2301SN-7	U-DFN2020-6	DB
AP2311SN-7	U-DFN2020-6	DC
AP23115N-7	U-DFN2020-6	DC



Package Outline Dimensions (All dimensions in mm.)

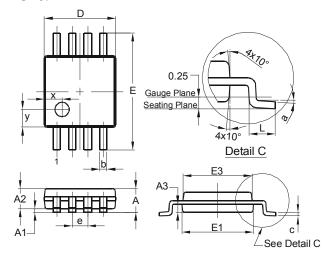
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

(1) Package type: SO-8



	SO-8					
Dim	Min	Max				
Α	-	1.75				
A1	0.10	0.20				
A2	1.30	1.50				
A3	0.15	0.25				
b	0.3	0.5				
D	4.85	4.95				
Е	5.90	6.10				
E1	3.85	3.95				
е	1.27	Тур				
h	-	0.35				
L	0.62	0.82				
θ	0°	8°				
All Dir	nensions	in mm				

(2) Package type: MSOP-8



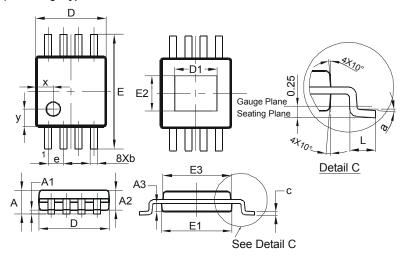
	MSOP-8							
Dim	Min	Max	Тур					
Α	-	1.10	-					
A1	0.05	0.15	0.10					
A2	0.75	0.95	0.86					
A3	0.29	0.49	0.39					
b	0.22	0.38	0.30					
С	0.08	0.23	0.15					
D	2.90	3.10	3.00					
Е	4.70	5.10	4.90					
E1	2.90	3.10	3.00					
E3	2.85	3.05	2.95					
е	-	ı	0.65					
Г	0.40	0.80	0.60					
а	0°	8°	4°					
Х	-	-	0.750					
у	•	-	0.750					
AII D)imen	sions	in mm					



Package Outline Dimensions (cont.) (All dimensions in mm.)

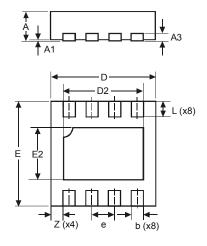
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

(3) Package type: MSOP-8EP



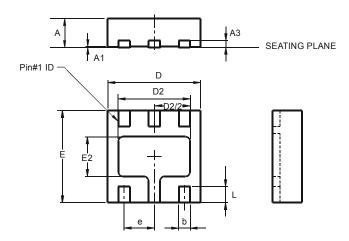
	MSOP-8EP					
Dim	Min	Max	Тур			
Α	-	1.10	-			
A1	0.05	0.15	0.10			
A2	0.75	0.95	0.86			
A3	0.29	0.49	0.39			
b	0.22	0.38	0.30			
С	0.08	0.23	0.15			
D	2.90	3.10	3.00			
D1	1.60	2.00	1.80			
Е	4.70	5.10	4.90			
E1	2.90	3.10	3.00			
E2	1.30	1.70	1.50			
E3	2.85	3.05	2.95			
е	-	-	0.65			
L	0.40	0.80	0.60			
а	0°	8°	4°			
х	-	-	0.750			
У	-	-	0.750			
All D	imensi	ons in	mm			

(4) Package type: U-DFN3030-8 Type E



U-DFN3030-8 Type E							
Dim	Dim Min Max Typ						
Α	0.57	0.63	0.60				
A1	0	0.05	0.02				
A3	-	-	0.15				
b	0.20	0.30	0.25				
D	2.95	3.05	3.00				
D2	2.15	2.35	2.25				
П	2.95	3.05	3.00				
е	-	1	0.65				
E2	1.40	1.60	1.50				
٦	0.30	0.60	0.45				
Ζ	_	-	0.40				
All [Dimens	ions in	mm				

(5) Package type: U-DFN2020-6



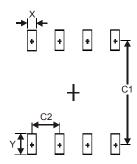
U-DFN2020-6				
Dim	Min	Max	Тур	
Α	0.57	0.63	0.60	
A1	0	0.05	0.03	
A3		_	0.15	
b	0.20	0.30	0.25	
D	1.95	2.075	2.00	
D2	1.45	1.65	1.55	
е	_	_	0.65	
Е	1.95	2.075	2.00	
E2	0.76	0.96	0.86	
L	0.30	0.40	0.35	
All Dimensions in mm				



Suggested Pad Layout

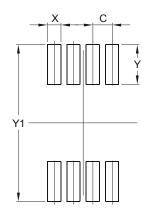
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(1) Package type: SO-8



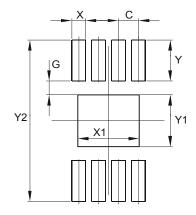
Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27

(2) Package type: MSOP-8



Dimensions	Value (in mm)
C	0.650
Х	0.450
Y	1.350
Y1	5.300

(3) Package type: MSOP-8EP



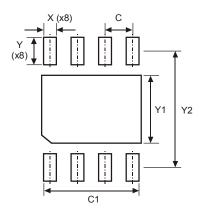
Dimensions	Value	
	(in mm)	
С	0.650	
G	0.450	
Х	0.450	
X1	2.000	
Y	1.350	
Y1	1.700	
Y2	5.300	



Suggested Pad Layout (cont.)

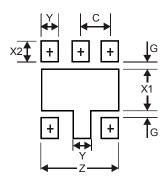
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(4) Package type: U-DFN3030-8 Type E



Dimensions	Value (in mm)
С	0.65
C1	2.35
Х	0.30
Y	0.65
Y1	1.60
Y2	2.75

(5) Package type: U-DFN2020-6

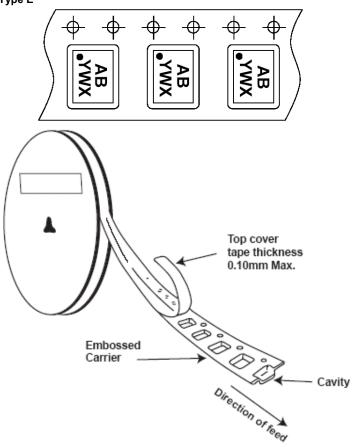


Dimensions	Value (in mm)
Z	1.67
G	0.15
X1	0.90
X2	0.45
Y	0.37
С	0.65



Taping Orientation (Note 11)

For U-DFN2020-6 and U-DFN3030-8 Type E



Note: 11. The taping orientation of the other package type can be found on our website at http://www.diodes.com/datasheets/ap02007.pdf



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